

AMENDMENT TO THE CLAIMS

1. (currently amended) A method of making an electrically programmable memory element, comprising:

providing a first dielectric layer, said first dielectric layer having a sidewall surface;

forming a conductive material sidewall spacer over said ~~first dielectric layer~~ sidewall surface;

forming a second dielectric layer over said conductive material sidewall spacer; and

forming a programmable resistance material in electrical contact with a peripheral top surface of said conductive sidewall spacer material.

Claims 2-6 (canceled)

7. (original) The method of claim 1, wherein said programmable resistance material is a phase-change material.

8. (original) The method of claim 1, wherein said programmable resistance material includes a chalcogen element.

9. (original) The method of claim 1, wherein said first dielectric layer and said second dielectric layer are formed of the same material.

10. (new) The method of claim 1, wherein said forming said conductive sidewall spacer step comprises:

forming a conductive material over said dielectric material; and

anisotropically etching said conductive material.

11. (new) The method of claim 10, wherein said forming said conductive material step comprises conformally depositing said conductive material over said dielectric material.

12. (new) A method of making an electrically programmable memory element, comprising:

forming a conductive sidewall spacer; and

forming a programmable resistance material in electrical communication with said sidewall spacer.

13. (new) The method of claim 1, wherein said programmable resistance material is in electrical contact with a top surface of said sidewall spacer.

14. (new) The method of claim 1, wherein said programmable resistance material consists essentially of a phase-change material.

15. (new) The method of claim 1, wherein said programmable resistance material comprises a chalcogen element.